N-Channel 75-V (D-S) MOSFET

Key Features:

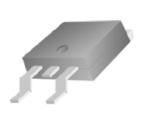
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

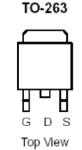
Typical	Дþ	plica	atior	ıs:
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- · Automotive Systems
- DC/DC Conversion Circuits
- Battery Powered Power Tools

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _□ (A)		
75	5.8 @ V _{GS} = 10V	90 ^a		
73	$7.3 @ V_{GS} = 4.5V$	90		







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage			75	V		
Gate-Source Voltage	V_{GS}	±20	V			
Continuous Drain Current a	I_D	90	Α			
Pulsed Drain Current ^b			240	^		
Continuous Source Current (Diode Conduction) ^a			110	Α		
Power Dissipation ^a	T _C =25°C	P_{D}	300	W		
Operating Junction and Storage Temperature Range			-55 to 175	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	62.5	°C/W		
Maximum Junction-to-Case	$R_{\theta JC}$	0.5	C/VV		

1

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

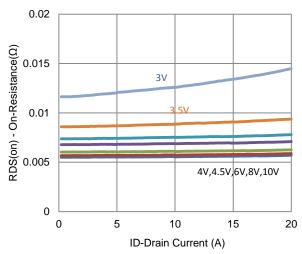
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	lana	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$			1	1 uA	
Zero Gate Voltage Brain Gurrent	I _{DSS}	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	uA	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	110			Α	
Drain-Source On-Resistance ^a	r	$V_{GS} = 10 \text{ V}, I_{D} = 45 \text{ A}$			5.8	mΩ	
Drain-Source On-Resistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 44 \text{ A}$			7.3	11122	
Forward Transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		34		S	
Diode Forward Voltage ^a	V_{SD}	$I_{S} = 55 \text{ A}, V_{GS} = 0 \text{ V}$		0.88		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = 37.5 \text{ V}, V_{GS} = 4.5 \text{ V},$		58		nC	
Gate-Source Charge	Q_{gs}	$V_{DS} = 37.3 \text{ V}, V_{GS} = 4.3 \text{ V},$ $I_{D} = 20 \text{ A}$		18			
Gate-Drain Charge	Q_gd	1D = 20 A		20			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 37.5 \text{ V}, R_{I} = 1.8 \Omega,$		21			
Rise Time	t _r	$V_{DS} = 37.5 \text{ V}, N_L - 1.0 \Omega,$ $I_D = 20 \text{ A},$		19		ns	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		168			
Fall Time	t _f	V GEN = 10 V, 1 (GEN = 0.22		40			
Input Capacitance	C _{iss}			10529			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		402		pF	
Reverse Transfer Capacitance	C_{rss}			284			

Notes

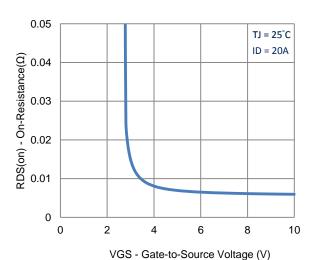
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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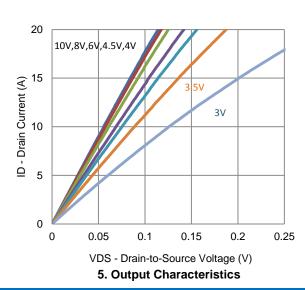
Typical Electrical Characteristics



1. On-Resistance vs. Drain Current



3. On-Resistance vs. Gate-to-Source Voltage

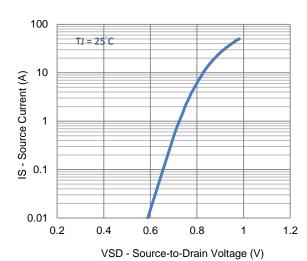


30
TJ = 25°C

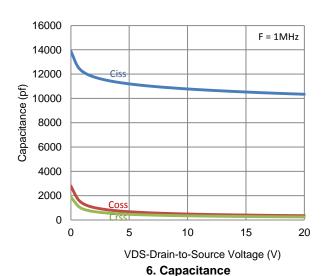
10
0
1 2 3 4 5

VGS - Gate-to-Source Voltage (V)

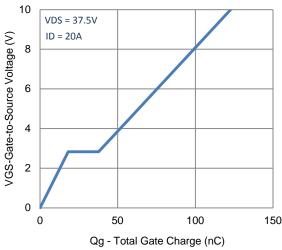
2. Transfer Characteristics

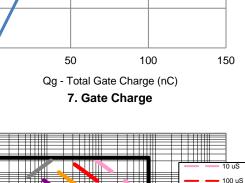


4. Drain-to-Source Forward Voltage



Typical Electrical Characteristics





100

100 us

100 us

100 us

1 ms

100 ms

1 sec

10 sec

100 sec

0.1

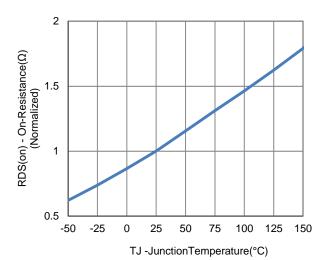
VDS Drain to Source Voltage (V)

100

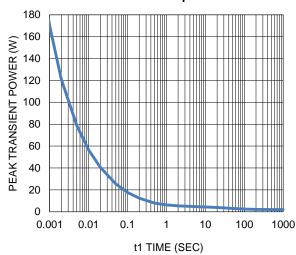
1000

9. Safe Operating Area

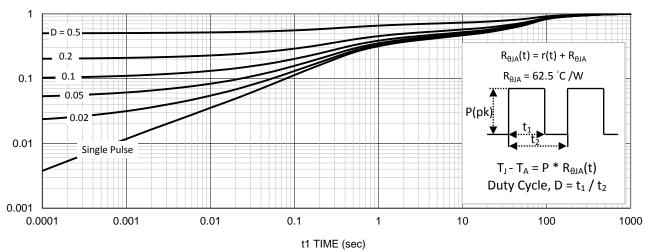
10



8. Normalized On-Resistance Vs Junction Temperature



10. Single Pulse Maximum Power Dissipation



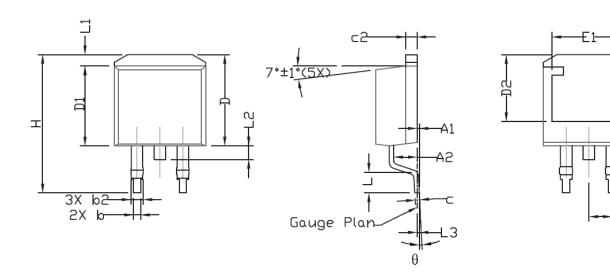
11. Normalized Thermal Transient Junction to Ambient

1000

0.01

0.1

Package Information



CVMDEI	DIMENS:	IONAL F	REQMTS	INCH	ES REG	2TM
SYMBOL	MIN	NDM	MAX	MIN	NDM	MAX
A	4,30	4.57	4,72	0.169	0.180	0.186
A1	0		0,25	0		0.010
A2	2,47	2.57	2,67	0.097	0.101	0.105
b	0.69	0,813	0.94	0.027	0.032	0.037
b2	1,17	1.27	1,45	0.046	0.050	0.057
C	0.48	0,50	0.60	0.019	0.020	0.024
c2	1,17	1.27	1.37	0.046	0,050	0,054
D	9,80	10.05	10,30	0.386	0,396	0.406
D1	8,64	8.78	9,65	0.340	0,346	0,380
D2	7.12	7,37	7,62	0.280	0,290	0,300
E	9,70	10.15	10.54	0.382	0,400	0.415
E1	8,00	8,20	8,40	0.315	0,323	0.331
е	2.	54 BSC	,	0.	100 BSC	_
H	14,99	15.24	15,49	0.590	0.600	0.610
L	1,78	2.29	2.79	0.070	0.090	0.110
L1	1,02	1.27	1.52	0.040	0.050	0,060
L2			1.75			0.069
L3		0,254			0.010	
θ	0°		8*	0°		8*

e 2X